



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Switching diode

1SS244

●Applications

High voltage switching
General purpose rectification

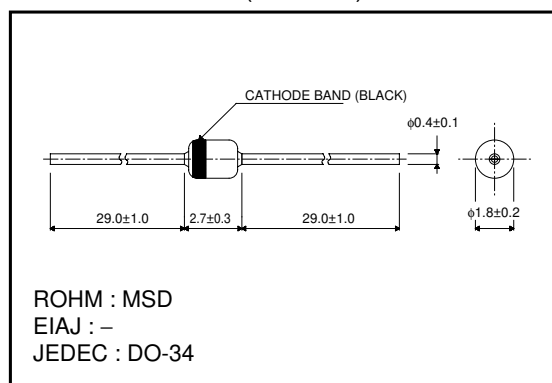
●Features

- 1) Glass sealed envelope. (MSD)
- 2) $V_{RM}=250V$ guaranteed.
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	250	V
DC reverse voltage	V_R	220	V
Peak forward current	I_{FM}	625	mA
Mean rectifying current	I_o	200	mA
Surge current (1s)	I_{surge}	1000	mA
Power dissipation	P	300	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65~+175	$^\circ\text{C}$

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.5	V	$I_F=200\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R=220\text{V}$
Capacitance between terminals	C_T	-	-	3	pF	$V_R=0\text{V}$, $f=1\text{MHz}$
Reverse recovery time	t_{rr}	-	-	75	ns	$I_F=20\text{mA}$, $I_R=20\text{mA}$, $R_L=50\Omega$

Diodes

●Electrical characteristics curves (Ta=25°C)

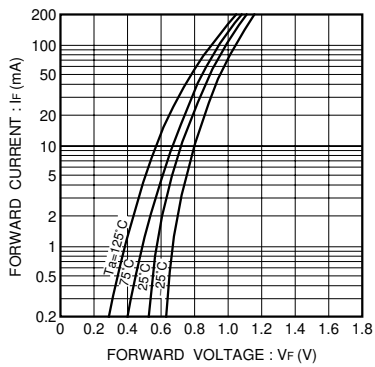


Fig.1 Forward characteristics

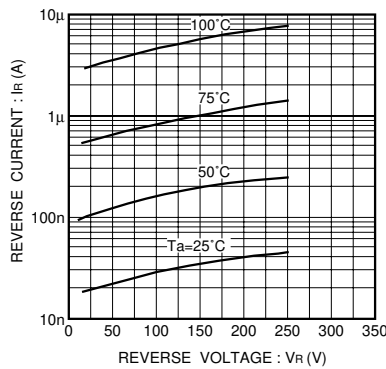


Fig.2 Reverse characteristics

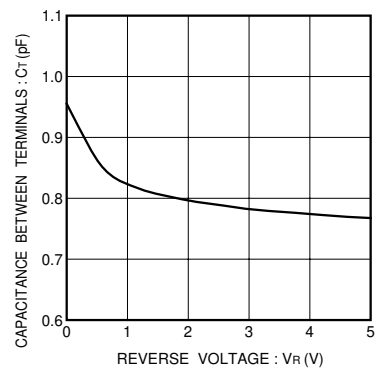


Fig.3 Capacitance between terminals characteristics

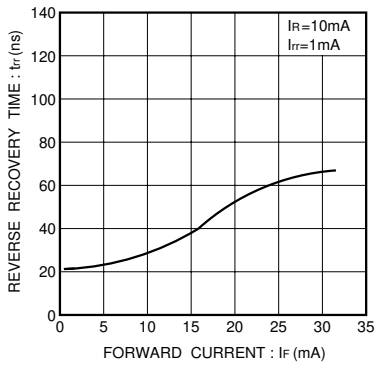


Fig.4 Reverse recovery time characteristics

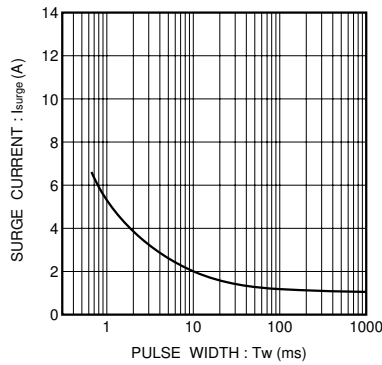


Fig.5 Surge current characteristics

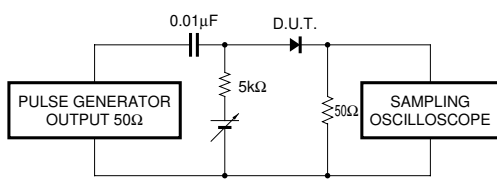


Fig.6 Reverse recovery time (tr) measurement circuit